
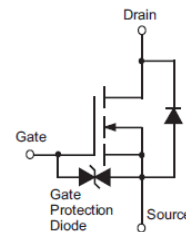
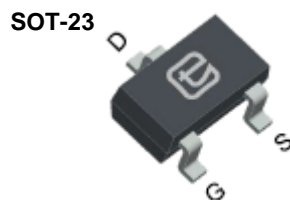


**60V N-Channel Trench MOSFET(Preliminary)**

<p>General Description</p> <ul style="list-style-type: none"> ● Trench Power technology ● Low $R_{DS(ON)}$ 2 Ω ● Low Gate Charge ● Low Input and Output Leakage ● 2000 V ESD Protection <p>Applications</p> <ul style="list-style-type: none"> ● Synchronous Rectification in DC/DC and AC/DC Converters ● Isolated DC/DC Converters in Telecom and Industrial 	<p>Product Summary</p> <table border="0"> <tr> <td>V_{DS}</td> <td>60V</td> </tr> <tr> <td>I_D (at $V_{GS}=10V$)</td> <td>0.35A</td> </tr> <tr> <td>$R_{DS(ON)}$ (at $V_{GS}=10V$)</td> <td>< 2Ω</td> </tr> </table> <p>100% UIS Tested</p> 	V_{DS}	60V	I_D (at $V_{GS}=10V$)	0.35A	$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 2 Ω
V_{DS}	60V						
I_D (at $V_{GS}=10V$)	0.35A						
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 2 Ω						



Part Number	Package Type	Form	Marking
TTX2N7002KA	SOT-23	Tape&Reel	7002KA

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^B	I_D	$T_C = 25^\circ\text{C}$	300
		$T_C = 100^\circ\text{C}$	190
Pulsed Drain Current ^A	I_{DM}	800	mA
Power Dissipation ^C	P_D	$T_C = 25^\circ\text{C}$	0.35
		$T_C = 100^\circ\text{C}$	0.14
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient	$R_{\theta JA}$	300	$^\circ\text{C/W}$



Electrical Characteristics($T_J = 25^\circ\text{C}$ unless otherwise noted)							
Symbol	Parameter	Conditions	Value			Units	
			Min	Typ	Max		
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D = 10\mu\text{A}, V_{GS} = 0\text{V}$	60	--	--	V	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$	$T_J = 25^\circ\text{C}$	--	--	1	μA
			$T_J = 100^\circ\text{C}$	--	--	500	
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	--	--	± 10	μA	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1	--	2.5	V	
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{V}, I_D = 0.35\text{A}$	--	--	2	Ω	
		$V_{GS} = 4.5\text{V}, I_D = 0.35\text{A}$	--	--	4	Ω	
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{V}, I_D = 0.35\text{A}$	100	--	--	ms	
V_{SD}	Diode Forward Voltage	$I_S = 0.2\text{A}, V_{GS} = 0\text{V}$	--	--	1.3	mV	
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$	--	40	--	pF	
C_{oss}	Output Capacitance		--	18	--		
C_{rss}	Reverse Transfer Capacitance		--	3.6	--		
SWITCHING PARAMETERS							
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS} = 4.5\text{V}, V_{DS} = 10\text{V}, I_D = 0.25\text{mA}$	--	0.8	--	nC	
Q_{gs}	Gate Source Charge		--	0.45	--		
Q_{gd}	Gate Drain Charge		--	0.2	--		
$T_{D(on)}$	Turn-On Delay Time	$V_{DD} = 30\text{V}, R_L = 150\Omega$ $I_D = 200\text{mA}, V_{GEN} = 10\text{V},$ $R_G = 10\Omega$	--	28	--	ns	
$T_{D(off)}$	Turn-Off Delay Time		--	40	--		

- A. Single pulse width limited by maximum junction temperature.
- B. The maximum current rating is package limited.
- C. The power dissipation P_D is based on $T_{J(MAX)} = 175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

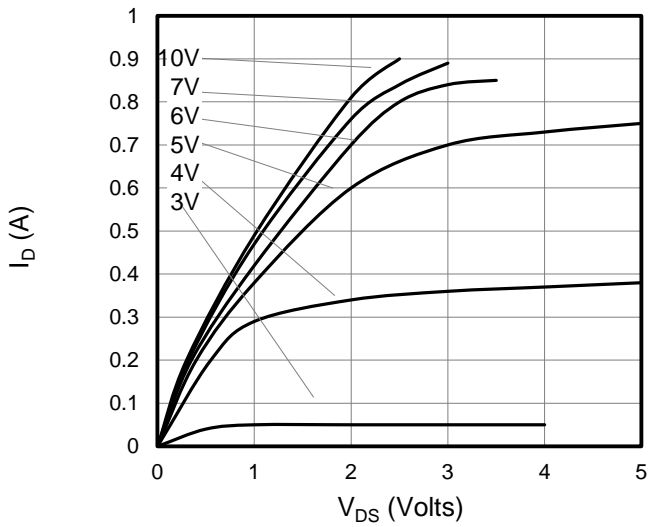


Figure 1: On-Region Characteristics

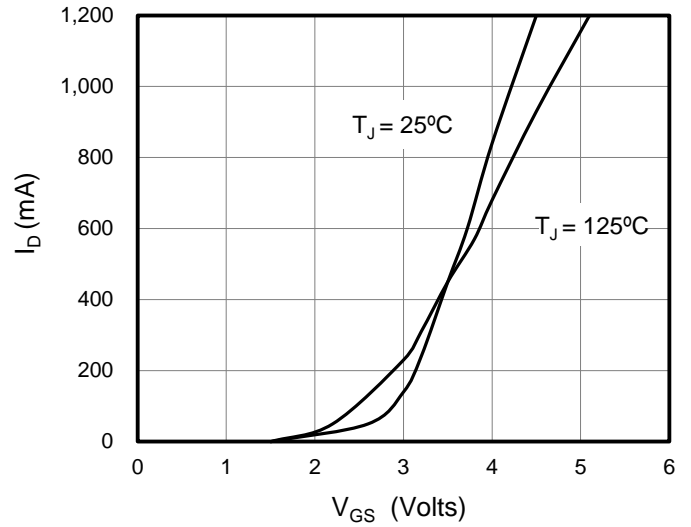


Figure 2: Transfer Characteristics

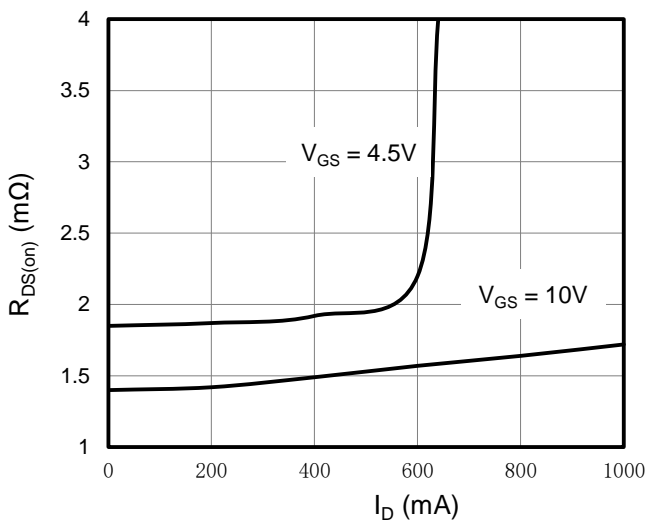


Figure 3: On-Resistance vs. Drain Current

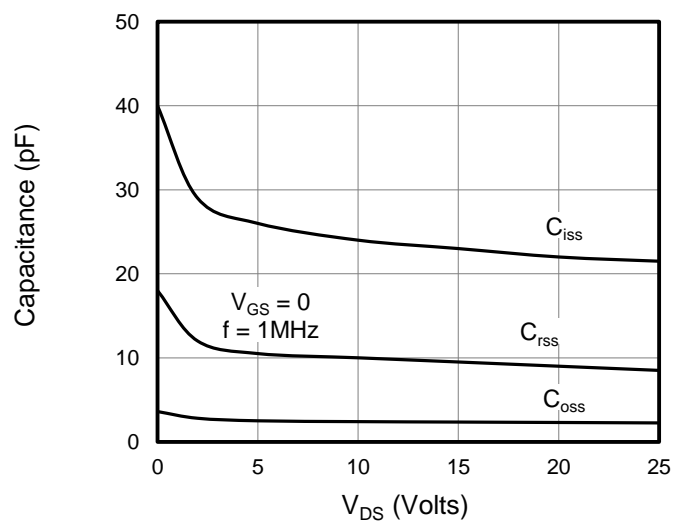


Figure 4: Capacitance Characteristics

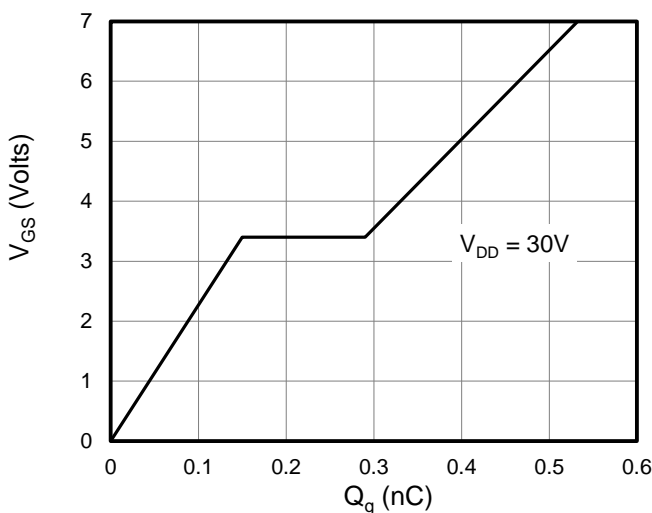


Figure 5: Gate Charge Characteristics

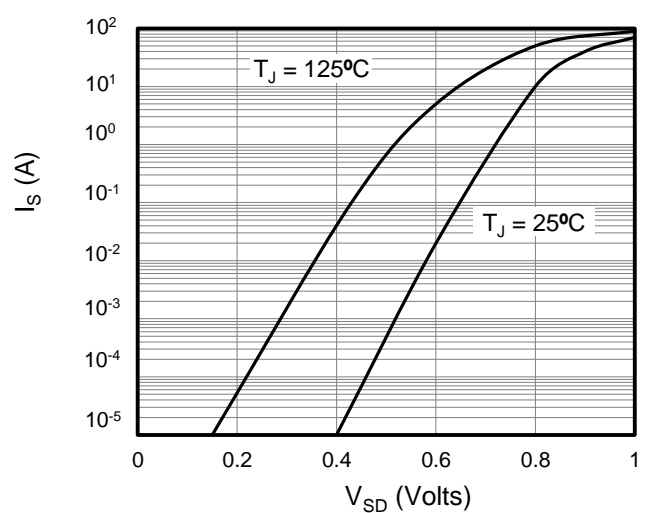


Figure 6: Body Diode Forward Voltage



Typical Characteristics $T_J = 25^{\circ}\text{C}$, unless otherwise noted

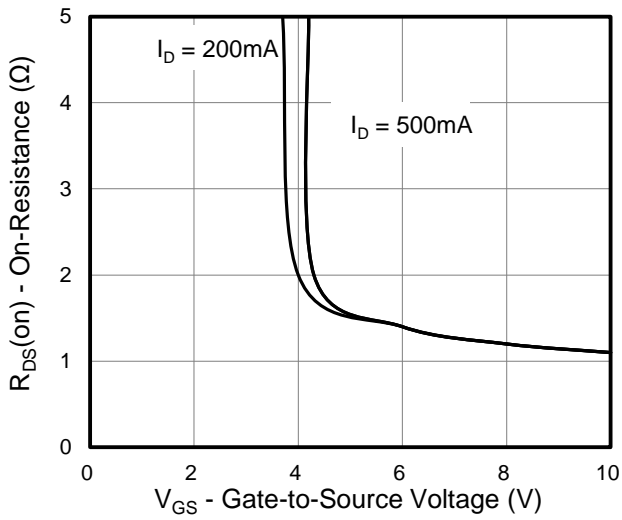


Figure 7: On-Resistance vs. Junction Temperature

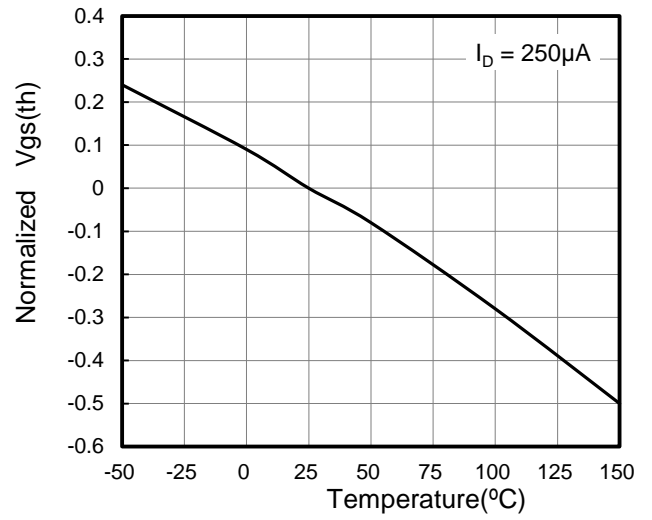


Figure 8: $V_{GS(th)}$ vs. Junction Temperature

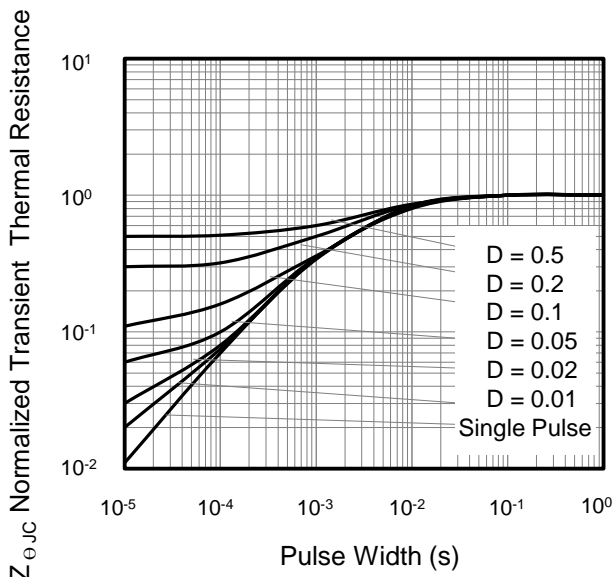


Figure 9: Normalized Transient Thermal Resistance

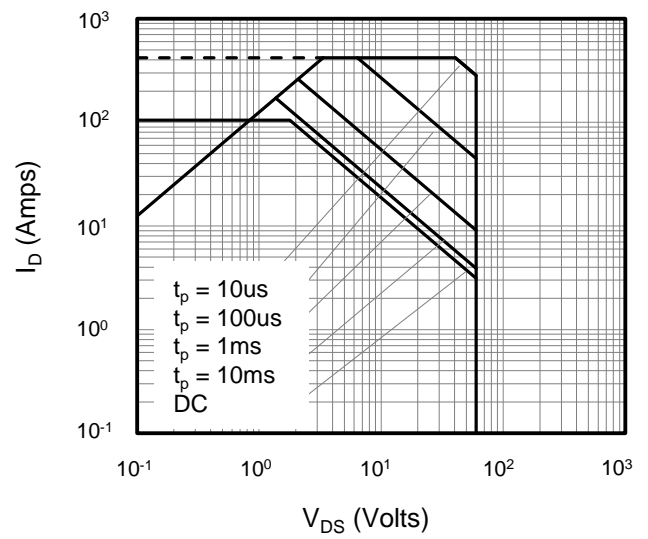


Figure 10: Safe Operating Area



Figure A: Gate Charge Test Circuit and Waveform



Figure B: Resistive Switching Test Circuit and Waveform

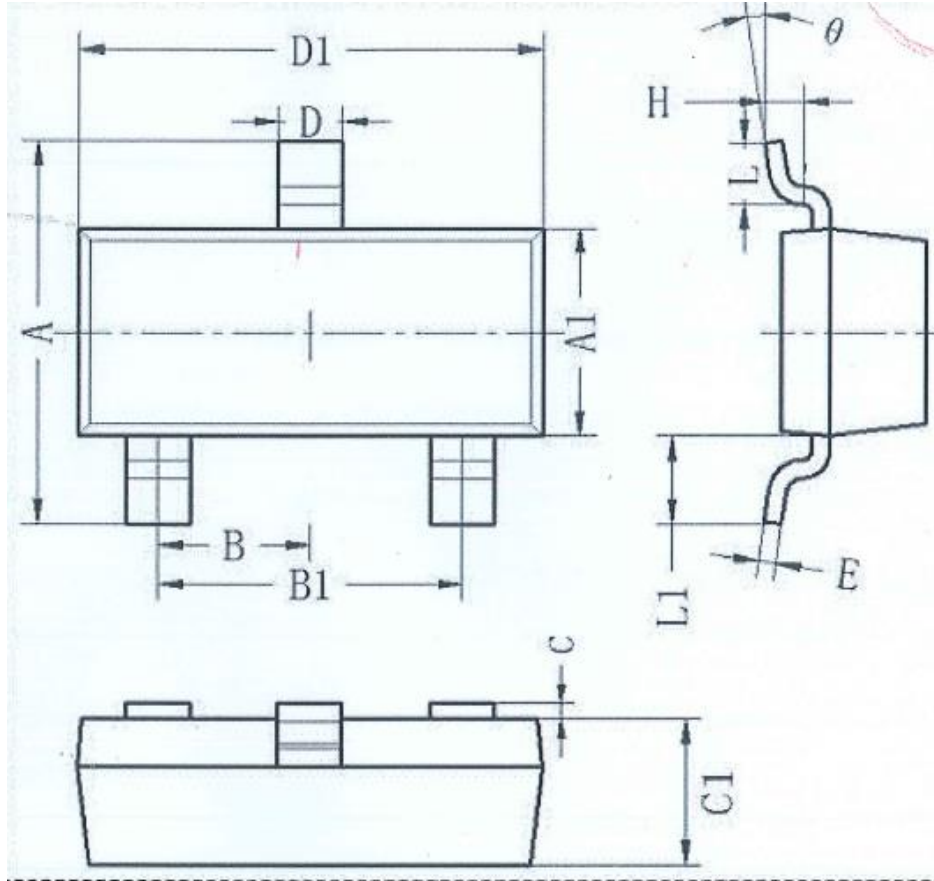


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





SOT-23(封装厂 N)



符号	标准	下公差	上公差	下限值	上限值
A	2.4	-0.15	0.15	2.25	2.55
A1	1.3	-0.1	0.1	1.2	1.4
B	0.95	-0.05	0.05	0.90	1.00
B1	1.9	-0.1	0.1	1.8	2
C	0.08	-0.06	0.06	0.02	0.14
C1	0.95	-0.05	0.05	0.9	1
D	0.4	-0.1	0.1	0.3	0.5
D1	2.9	-0.1	0.1	2.8	3
E	0.1	-0.03	0.03	0.07	0.13
H	0.25	-0.03	0.03	0.22	0.28
L	0.4	-0.1	0.1	0.3	0.5
L1	0.55	-0.07	0.07	0.48	0.62
θ	4	-3	3		7



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